

Schottky Barrier Rectifiers

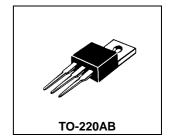
Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

- * Low Forward Voltage.
- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- * 150 Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory

Flammability Classification 94V-O

SCHOTTKY BARRIER RECTIFIERS

20 AMPERES 120 VOLTS



MAXIMUM RATINGS

Characteristic	Symbol	S20C120C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	120	CV.
RMS Reverse Voltage	V _{R(RMS)}	84 C	V
Average Rectifier Forward Current Total Device (Rated V _R),T _C =100	I _{F(AV)}	10 20	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	20	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	200	А
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +125	

$\begin{array}{c|c} & B \\ \hline M & D \\ \hline 1 & 2 & 3 & G \\ \hline & D & K \\ \hline & M & D \\$

DIM	MILLIMETERS				
ווים	MIN	MAX			
Α	14.68	15.32			
В	9.78	10.42			
С	6.02	6.52			
D	13.06	14.62			
E	3.57	4.07			
F	4.84	5.32			
G	1.12	1.36			
Н	0.72	0.96			
ı	4.22	4.98			
J	1.14	1.38			
K	2.20	2.98			
L	0.33	0.55			
M	2.48	2.98			
Ω	3.70	3 90			

ELECTRIAL CHARACTERISTICS

Characteristic	Symbol	S20C120C	Unit
Maximum Instantaneous Forward Voltage ($I_F = 10 \text{ Amp } T_C = 25$) ($I_F = 10 \text{ Amp } T_C = 125$)	V _F	0.85 0.68	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _C = 25) (Rated DC Voltage, T _C = 125)	I _R	0.5 20	mA

